BC856A - BC858C

PNP SMALL SIGNAL TRANSISTOR

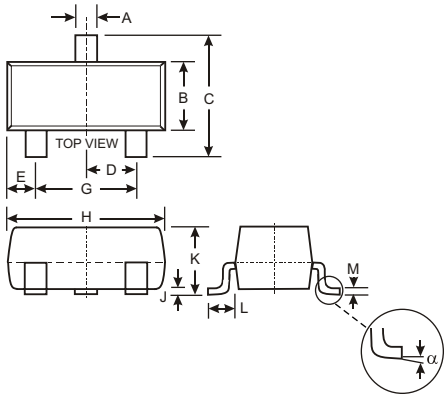
Features

- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- Moisure Sensitivity Level 1
- Ideally Suited for Automatic Insertion
- 150°C Junction Temperature
- For Switching and AF Amplifier Applications
- Halogen free available upon request by adding suffix "-HF"

Mechanical Data

- Case: SOT-23, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Weight: 0.008 grams (approx.)

RoHS COMPLIANT



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Charateristic		Symbol	Value	Unit
Collector-Base Voltage	BC856 BC857 BC858	V_{CBO}	-80 -50 -30	V
Collector-Emitter Voltage	BC856 BC857 BC858	V_{CEO}	-65 -45 -30	V
Emitter-Base Voltage		V_{EBO}	-5.0	V
Collector Current		I_C	-100	mA
Peak Collector Current		I_{CM}	-200	mA
Peak Emitter Current		I_{EM}	-200	mA
Power Dissipation@T_s=50°C(Note1)		P_d	200	mW
Operating & Storage Temperature		T_j, T_{STG}	-55~150	°C

Note: 1. Package mounted on ceramic substrate 0.7mm X 2.5cm² area.

2. Current gain subgroup " C" is not available for BC856

BC856A thru BC858C

Electrical Characteristics @ T_A =25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 3)	BC856 BC857 BC858	$V_{(BR)CBO}$	-80 -50 -30	— — —	— — —	V	I_C = 10μA, I_B = 0
Collector-Emitter Breakdown Voltage (Note 3)	BC856 BC857 BC858	$V_{(BR)CEO}$	-65 -45 -30	— — —	— — —	V	I_C = 10mA, I_B = 0
Emitter-Base Breakdown Voltage (Note 3)		$V_{(BR)EBO}$	-5	—	—	V	I_E = 1μA, I_C = 0
H-Parameters Small Signal Current Gain	Current Gain Group A B C	h_{fe} h_{fe} h_{fe}	— — —	200 330 600	— — —	— — —	
Input Impedance	Current Gain Group A B C	h_{ie} h_{ie} h_{ie}	— — —	2.7 4.5 8.7	— — —	kΩ kΩ kΩ	V_{CE} = -5.0V, I_C = -2.0mA, f = 1.0kHz
Output Admittance	Current Gain Group A B C	h_{oe} h_{oe} h_{oe}	— — —	18 30 60	— — —	μS μS μS	
Reverse Voltage Transfer Ratio	Current Gain Group A B C	h_{re} h_{re} h_{re}	— — —	$1.5x10^{-4}$ $2x10^{-4}$ $3x10^{-4}$	— — —	— — —	
DC Current Gain (Note 3)	Current Group A B C	h_{FE}	125 220 420	180 290 520	250 475 800	—	V_{CE} = -5.0V, I_C = -2.0mA
Thermal Resistance, Junction to Substrate Backside		$R_{\theta JSB}$	—	—	320	°C/W	Note 1
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$	—	—	625	°C/W	Note 1
Collector-Emitter Saturation Voltage (Note 3)		$V_{CE(SAT)}$	—	-75 -250	-300 -650	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5.0mA
Base-Emitter Saturation Voltage (Note 3)		$V_{BE(SAT)}$	— —	-700 -850	—	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5.0mA
Base-Emitter Voltage (Note 3)		$V_{BE(ON)}$	-600 —	-650 —	-750 -820	mV	V_{CE} = -5.0V, I_C = -2.0mA V_{CE} = -5.0V, I_C = -10mA
Collector-Cutoff Current (Note 3)	BC856 BC857 BC858	I_{CES} I_{CES} I_{CES} I_{CBO} I_{CBO}	— — — — —	— — — — —	-15 -15 -15 -15 -4.0	nA nA nA nA μA	V_{CE} = -80V V_{CE} = -50V V_{CE} = -30V V_{CB} = -30V V_{CB} = -30V, T_A = 150°C
Gain Bandwidth Product		f_T	100	200	—	MHz	V_{CE} = -5.0V, I_C = -10mA, f = 100MHz
Collector-Base Capacitance		C_{CBO}	—	3	—	pF	V_{CB} = -10V, f = 1.0MHz
Noise Figure		NF	—	2	10	dB	V_{CE} = -5.0V, I_C = 200μA, R_S = 2kΩ, f = 1kHz, Δf = 200Hz

Notes: 1. Package mounted on ceramic substrate 0.7mm x 2.5cm² area.
2. Current gain subgroup “C” is not available for BC856.
3. Short duration pulse test to minimize self-heating effect.